# 2SD1367

## Silicon NPN Epitaxial

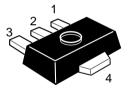
# **HITACHI**

### **Application**

- Low frequency power amplifier
- Complementary pair with 2SB1001

#### Outline

UPAK



- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector (Flange)



## 2SD1367

#### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{\text{CBO}}$	20	V
Collector to emitter voltage	V <sub>CEO</sub>	16	V
Emitter to base voltage	$V_{EBO}$	6	V
Collector current	I <sub>c</sub>	2	A
Collector peak current	i <sub>C(peak)</sub> *1	3	A
Collector power dissipation	P <sub>C</sub> *2	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10 ms, Duty cycle  $\leq$  20%.

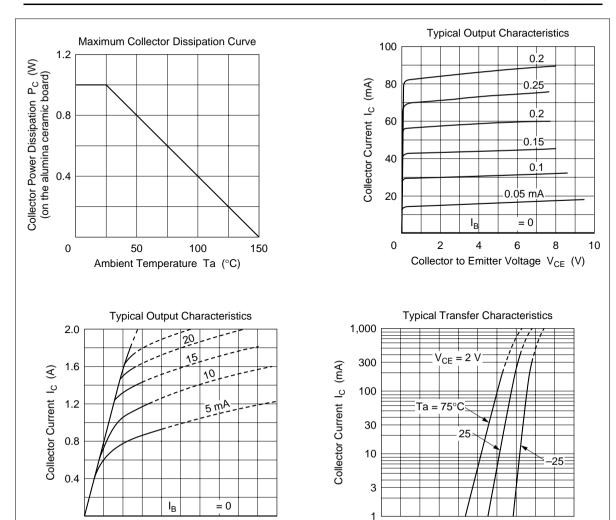
2. Value on the alumina ceramic board (12.5  $\times$  20  $\times$  0.7 mm)

#### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	16	_	_	V	$I_{C}$ = 1 mA, $R_{BE}$ = $\infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	_	_	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	0.1	μΑ	V <sub>CB</sub> = 16 V, I <sub>E</sub> = 0
Emitter cutoff current	I <sub>EBO</sub>	_		0.1	μΑ	$V_{EB} = 5 \text{ V}, I_{C} = 0$
DC current transfer ratio	h <sub>FE</sub> *1	100	_	500		$V_{CE} = 2 \text{ V}, I_{C} = 0.1 \text{ A}, \text{ Pulse}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	0.15	0.3	V	$I_{c} = 1 \text{ A}, I_{B} = 0.1 \text{ A}, \text{ Pulse}$
Base to emitter saturation voltage	$V_{BE(sat)}$	_	0.9	1.2	V	I <sub>C</sub> = 1 A, I <sub>B</sub> = 0.1 A, Pulse
Gain bandwidth product	f <sub>T</sub>	_	100	_	MHz	$V_{CE} = 2 \text{ V}, I_{C} = 10 \text{ mA}$
Collector output capacitance	Cob	_	20	_	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

Note: 1. The 2SD1367 is grouped by  $h_{\text{FE}}$  as follows.

Mark	ВА	ВВ	ВС
h <sub>FE</sub>	100 to 200	160 to 320	250 to 500



0.4

8.0

0

1.2

Collector to Emitter Voltage V<sub>CE</sub> (V)

1.6

2.0

0

0.2

0.4

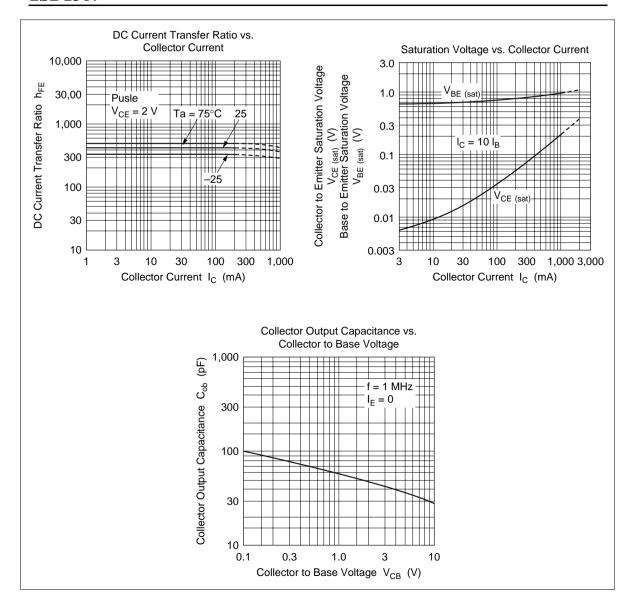
0.6

Base to Emitter Voltage  $V_{BE}$  (V)

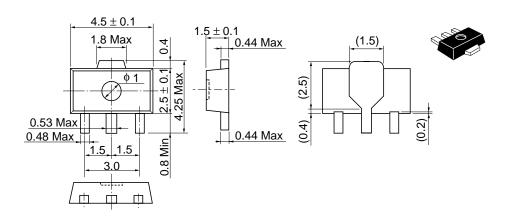
8.0

1.0

## 2SD1367



Unit: mm



Hitachi Code	UPAK
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.050 g

#### **Cautions**

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